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#### June 2014

FDMA420NZ Single N-Channel 2.5V Specified PowerTrench<sup>®</sup> MOSFET

## Single N-Channel 2.5V Specified PowerTrench<sup>®</sup> MOSFET

## 20V, 5.7A, 30m $\Omega$

## **General Description**

This Single N-Channel MOSFET has been designed using Fairchild Semiconductor's advanced Power Trench process to optimize the  $\rm R_{DS}(on)~@V_{GS}=2.5V$  on special MicroFET leadframe.

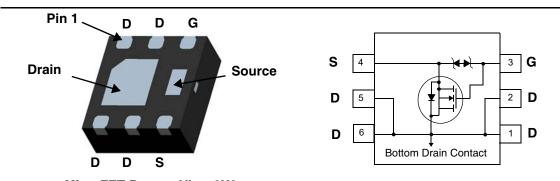
## Applications

Li-lon Battery Pack



## Features

- $R_{DS(on)} = 30m\Omega @ V_{GS} = 4.5 V, I_D = 5.7A$
- $R_{DS(on)} = 40m\Omega$  @  $V_{GS} = 2.5$  V,  $I_D = 5.0$ A
- Low Profile-0.8mm maximum-in the new package MicroFET 2x2 mm
- HBM ESD protection level > 2.5k V typical (Note 3)
- Free from halogenated compounds and antimony oxides
- RoHS Compliant



#### MicroFET Bottom View 2X2

### Absolute Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		20	V
V <sub>GSS</sub>	Gate-Source Voltage		±12	V
I_	Drain Current -Continuous	(Note 1a)	5.7	Α
D	-Pulsed		24	~
D	Power dissipation (Steady State)	(Note 1a)	2.4	w
D		(Note 1b)	0.9	~~~
Г <sub>Ј</sub> , Т <sub>STG</sub>	Operating and Storage Junction Temperature Range		-55 to +150	°C

## **Thermal Characteristics**

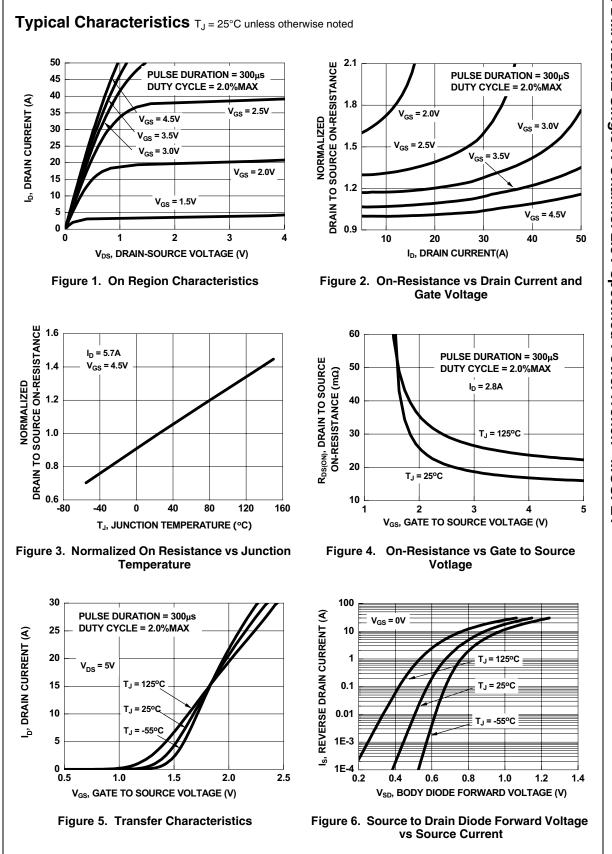
$R_{\thetaJA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	52	°C/W
$R_{ hetaJA}$	Thermal Resistance, Junction-to-Ambient	(Note 1b)	145	0/00

## Package Marking and Ordering Information

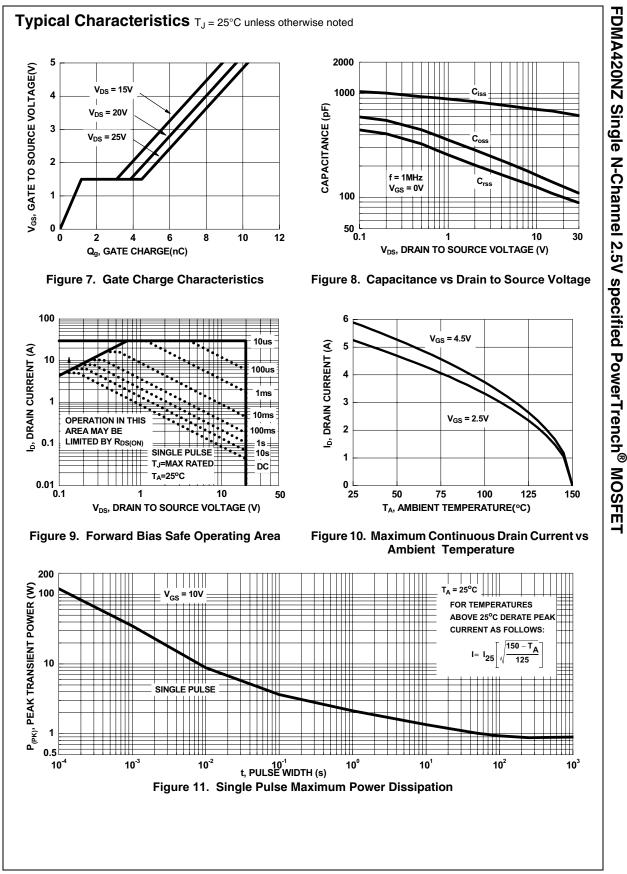
Device Marking	Device	Reel Size	Tape Width	Quantity
420	FDMA420NZ	7"	8 mm	3000 units

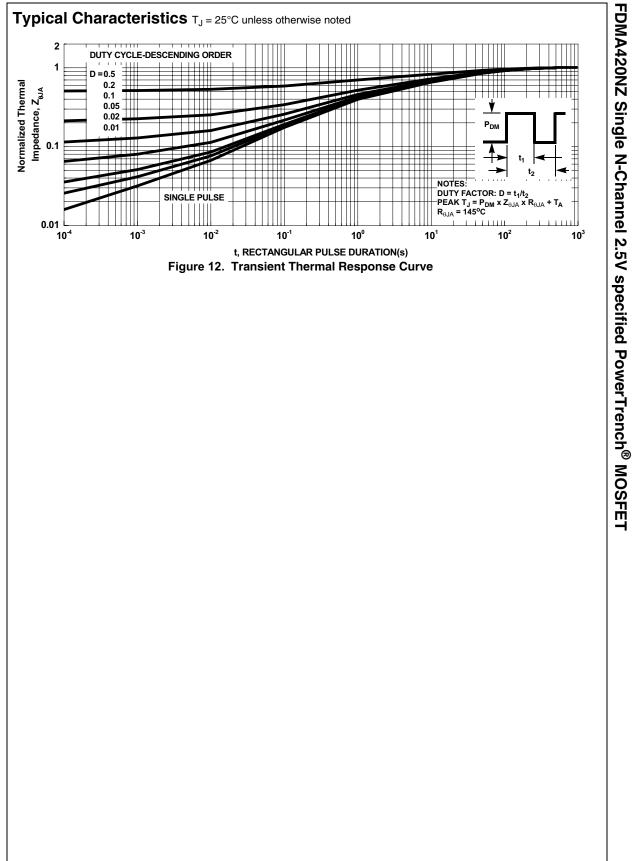
$\begin{array}{c c} age & V_{GS} = 0V \ , \ \ I_D = 250 \mu A \\ \mbox{ Irre} & I_D = 250 \mu A , \\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$	20 0.6	12 0.83 -3.1 16.8 17.3	1 ±10 1.5 30	V mV/°C μΑ μΑ V mV/°C
$\begin{tabular}{ c c c c c } \hline U & U & U & U & U & U & U & U & U & U$		0.83 -3.1 16.8	±10 1.5 30	mV/°C μA μA
$\label{eq:linear} \begin{array}{ c c c c c } \text{ure} & I_D = 250 \mu\text{A}, \\ \text{Referenced to } 25^\circ\text{C} \\ \hline \text{Pot} & V_{DS} = 16\text{V}, \ V_{GS} = 0\text{V}, \\ \hline V_{GS} = \pm 12\text{V}, \ V_{DS} = 0\text{V} \\ \hline & V_{DS} = V_{GS}, \ I_D = 250 \mu\text{A} \\ \hline & I_D = 250 \mu\text{A}, \\ \text{Referenced to } 25^\circ\text{C} \\ \hline & V_{GS} = 4.5\text{V}, \ I_D = 5.7\text{A} \\ \hline & V_{GS} = 4.0\text{V}, \ I_D = 5.7\text{A} \\ \hline & V_{GS} = 2.5\text{V}, \ I_D = 5.0\text{A} \\ \hline \end{array}$	0.6	0.83 -3.1 16.8	±10 1.5 30	μΑ μΑ V
ent $V_{DS} = 16V, V_{GS} = 0V,$ $V_{GS} = \pm 12V, V_{DS} = 0V$ $V_{DS} = V_{GS}, I_D = 250\mu A$ $I_D = 250\mu A,$ Referenced to 25°C $V_{GS} = 4.5V, I_D = 5.7A$ $V_{GS} = 4.0V, I_D = 5.7A$ $V_{GS} = 3.1V, I_D = 5.0A$ $V_{GS} = 2.5V, I_D = 5.0A$	0.6	-3.1 16.8	±10 1.5 30	μA V
$V_{GS} = \pm 12V, V_{DS} = 0V$ $V_{DS} = V_{GS}, I_D = 250\mu A$ $I_D = 250\mu A,$ Referenced to 25°C $V_{GS} = 4.5V, I_D = 5.7A$ $V_{GS} = 4.0V, I_D = 5.7A$ $V_{GS} = 3.1V, I_D = 5.0A$ $V_{GS} = 2.5V, I_D = 5.0A$	0.6	-3.1 16.8	±10 1.5 30	μA V
$V_{DS} = V_{GS}, I_D = 250\mu A$ $I_D = 250\mu A,$ Referenced to 25°C $V_{GS} = 4.5V, I_D = 5.7A$ $V_{GS} = 4.0V, I_D = 5.7A$ $V_{GS} = 3.1V, I_D = 5.0A$ $V_{GS} = 2.5V, I_D = 5.0A$	0.6	-3.1 16.8	1.5 30	V
$I_{D} = 250 \mu A,$ Referenced to 25°C $V_{GS} = 4.5V, I_{D} = 5.7A$ $V_{GS} = 4.0V, I_{D} = 5.7A$ $V_{GS} = 3.1V, I_{D} = 5.0A$ $V_{GS} = 2.5V, I_{D} = 5.0A$	0.6	-3.1 16.8	30	-
$I_{D} = 250 \mu A,$ Referenced to 25°C $V_{GS} = 4.5V, I_{D} = 5.7A$ $V_{GS} = 4.0V, I_{D} = 5.7A$ $V_{GS} = 3.1V, I_{D} = 5.0A$ $V_{GS} = 2.5V, I_{D} = 5.0A$		-3.1 16.8	30	-
$\begin{tabular}{ c c c c c c } \hline Referenced to 25^{\circ}C \\ \hline V_{GS} = 4.5V, \ I_D = 5.7A \\ \hline V_{GS} = 4.0V, \ I_D = 5.7A \\ \hline V_{GS} = 3.1V, \ I_D = 5.0A \\ \hline V_{GS} = 2.5V, \ I_D = 5.0A \\ \hline \end{tabular}$		16.8		mV/°C
$\frac{V_{GS} = 4.5V, \ I_D = 5.7A}{V_{GS} = 4.0V, \ I_D = 5.7A}$ tance $\frac{V_{GS} = 3.1V, \ I_D = 5.0A}{V_{GS} = 2.5V, \ I_D = 5.0A}$				
tance $\frac{V_{GS} = 4.0V, \ I_D = 5.7A}{V_{GS} = 3.1V, \ I_D = 5.0A}$ $\frac{V_{GS} = 2.5V, \ I_D = 5.0A}{V_{GS} = 2.5V, \ I_D = 5.0A}$				
tance $V_{GS} = 3.1V, I_D = 5.0A$ $V_{GS} = 2.5V, I_D = 5.0A$		-	31	_
$V_{GS} = 2.5V, I_D = 5.0A$		18.9	33	
		21.2	40	mΩ
$V_{GS} = 4.5V, I_D = 5.7A, T_J = 150^{\circ}C$		24.8	44	1
		28.3		S
				_
		701	005	<b>-</b>
V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V,				pF ∽⊑
f = 1.0MHz	-			pF
			190	pF Ω
V <sub>DD</sub> = 10V, I <sub>D</sub> = 1A		9.8 8.6	20 18	ns ns
$V_{GS} = 4.5V, R_{GEN} = 6\Omega$		21.5	43	ns
		8.6	18	ns
		8.8	12	nC
		0.9	2	nC
V <sub>GS</sub> = 4.5 V		2.4	4	nC
cs and Maximum Batings				
cs and Maximum Ratings			2.0	A
ource Diode Forward Current		0.69	2.0 1.2	AV
ource Diode Forward Current		0.69		
	<pre>     f = 1.0MHz     V_DD = 10V, I_D = 1A </pre>	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz f = 1.0MHz $V_{DD} = 10V, I_D = 1A$ $V_{GS} = 4.5V, R_{GEN} = 6\Omega$ $V_{DS} = 10V, I_D = 5.7A,$	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $

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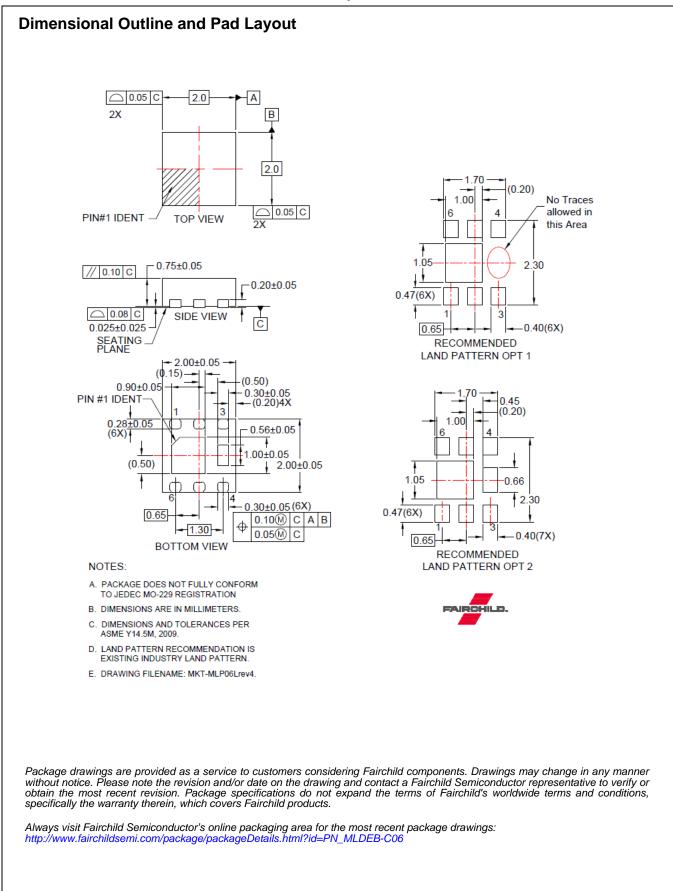


FDMA420NZ Single N-Channel 2.5V specified PowerTrench<sup>®</sup> MOSFET





## **Preliminary Datasheet**



FDMA420NZ Single N-Channel 2.5V specified PowerTrench<sup>®</sup> MOSFET



Rev. 168

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